



## DESCRIPTION

The PZT2222A is available in SOT-223 package

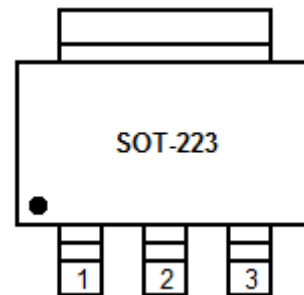
## ORDERING INFORMATION

| Package Type                             | Part Number        |
|------------------------------------------|--------------------|
| SOT-223                                  | PZT2222A           |
| Note                                     | SPQ: 1,000pcs/Reel |
| AiT provides all RoHS Compliant Products |                    |

## FEATURES

- Power Dissipation  
 $P_{CM}$ : 1W ( $T_{amb}=25^{\circ}C$ )
- Collector Current  
 $I_{CM}$ : 0.6A
- Collector-Base Voltage  
 $V_{(BR)CBO}$ : 75V
- Operating and Storage Junction Temperature Range  
 $T_J, T_{STG}$ :  $-55^{\circ}C$  to  $150^{\circ}C$
- Available in SOT-223 package

## PIN DESCRIPTION



1. BASE
2. COLLECTOR
3. EMITTER



## ELECTRICAL CHARACTERISTICS

T<sub>amb</sub>=25°C, unless otherwise specified

| Parameter                             | Symbol               | Conditions                                              | Min. | Max. | Unit |
|---------------------------------------|----------------------|---------------------------------------------------------|------|------|------|
| Collector-Base Breakdown Voltage      | V <sub>(BR)CBO</sub> | I <sub>C</sub> =10μA, I <sub>E</sub> =0                 | 75   |      | V    |
| Collector-Emitter Breakdown Voltage   | V <sub>(BR)CEO</sub> | I <sub>C</sub> =10mA, I <sub>B</sub> =0                 | 40   |      | V    |
| Emitter-Base Breakdown Voltage        | V <sub>(BR)EBO</sub> | I <sub>E</sub> =10μA, I <sub>C</sub> =0                 | 6.0  |      | V    |
| Collector Cut-Off Current             | I <sub>CBO</sub>     | V <sub>CB</sub> =60V, I <sub>E</sub> =0                 |      | 0.01 | μA   |
| Emitter Cut-Off Current               | I <sub>EBO</sub>     | V <sub>EB</sub> =3.0V, I <sub>C</sub> =0                |      | 0.01 | μA   |
| DC Current Gain                       | h <sub>FE(1)</sub>   | I <sub>C</sub> =0.1mA, V <sub>CE</sub> =10V             | 35   |      | -    |
|                                       | h <sub>FE(2)</sub>   | I <sub>C</sub> =1.0mA, V <sub>CE</sub> =10V             | 50   |      | -    |
|                                       | h <sub>FE(3)</sub>   | I <sub>C</sub> =10mA, V <sub>CE</sub> =10V              | 75   |      | -    |
|                                       | h <sub>FE(4)</sub>   | I <sub>C</sub> =150mA, V <sub>CE</sub> =10V             | 100  | 300  | -    |
|                                       | h <sub>FE(5)</sub>   | I <sub>C</sub> =150mA, V <sub>CE</sub> =1.0V            | 50   |      | -    |
|                                       | h <sub>FE(6)</sub>   | I <sub>C</sub> =500mA, V <sub>CE</sub> =10V             | 40   |      | -    |
| Collector- Emitter Saturation Voltage | V <sub>CE(sat)</sub> | I <sub>C</sub> =500mA, I <sub>B</sub> =50mA             |      | 1.0  | V    |
|                                       |                      | I <sub>C</sub> =150mA, I <sub>B</sub> =15mA             |      | 0.3  |      |
| Base-Emitter Saturation Voltage       | V <sub>BE(sat)</sub> | I <sub>C</sub> =500mA, I <sub>B</sub> =50mA             |      | 2.0  | V    |
|                                       |                      | I <sub>C</sub> =150mA, I <sub>B</sub> =15mA             | 0.6  | 1.2  |      |
| Transition Frequency                  | f <sub>T</sub>       | I <sub>C</sub> =20mA, V <sub>CE</sub> =20V,<br>f=100MHz | 300  |      | MHz  |
| Output Capacitance                    | C <sub>ob</sub>      | I <sub>E</sub> =0, V <sub>CB</sub> =10V, f=1MHz         |      | 8    | pF   |
| Delay Time                            | t <sub>d</sub>       | V <sub>CC</sub> =30V, I <sub>C</sub> =150mA             |      | 10   | nS   |
| Rise Time                             | t <sub>r</sub>       | V <sub>BE(off)</sub> =0.5V, I <sub>B1</sub> =15mA       |      | 25   | nS   |
| Storage Time                          | t <sub>s</sub>       | V <sub>CC</sub> =30V, I <sub>C</sub> =150mA,            |      | 225  | nS   |
| Fall Time                             | t <sub>f</sub>       | I <sub>B1</sub> = I <sub>B2</sub> =15mA                 |      | 60   | nS   |



**SWITCHING TIME EQUIVALENT TEST CIRCUITS**

Figure. 1 Turn-on Time

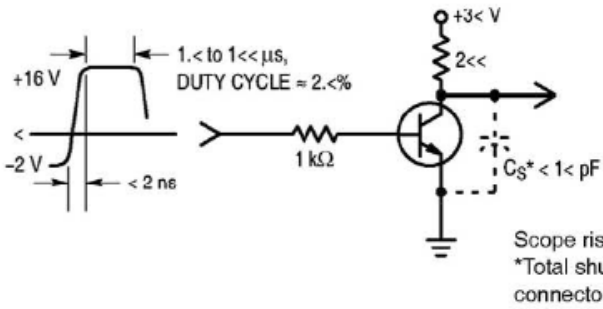


Figure. 2 Turn-off Time

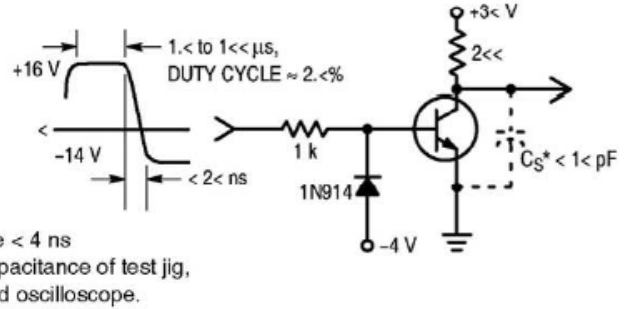


Figure. 3 DC Current Gain

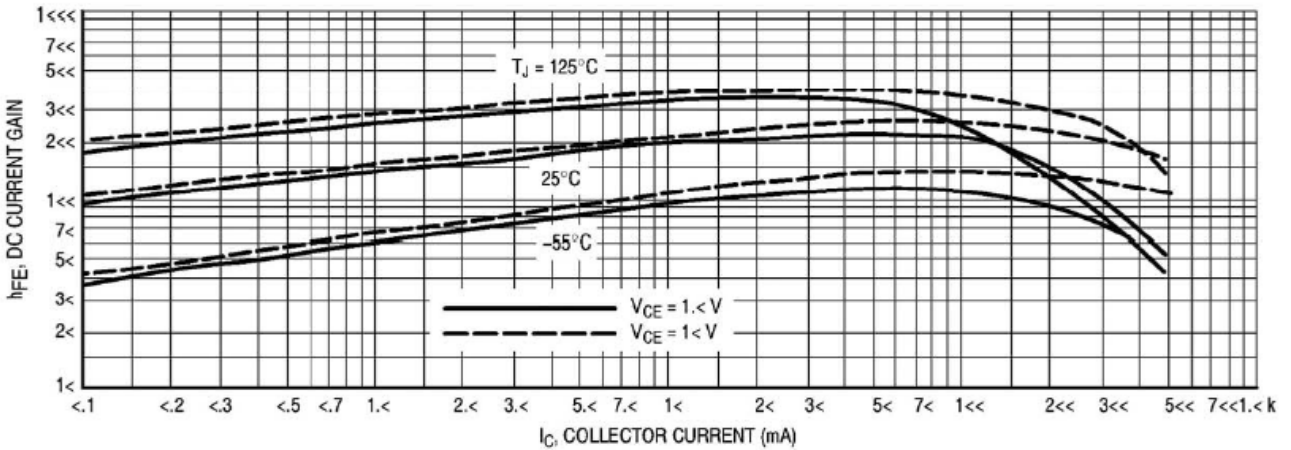


Figure. 4 Collector Saturation Region

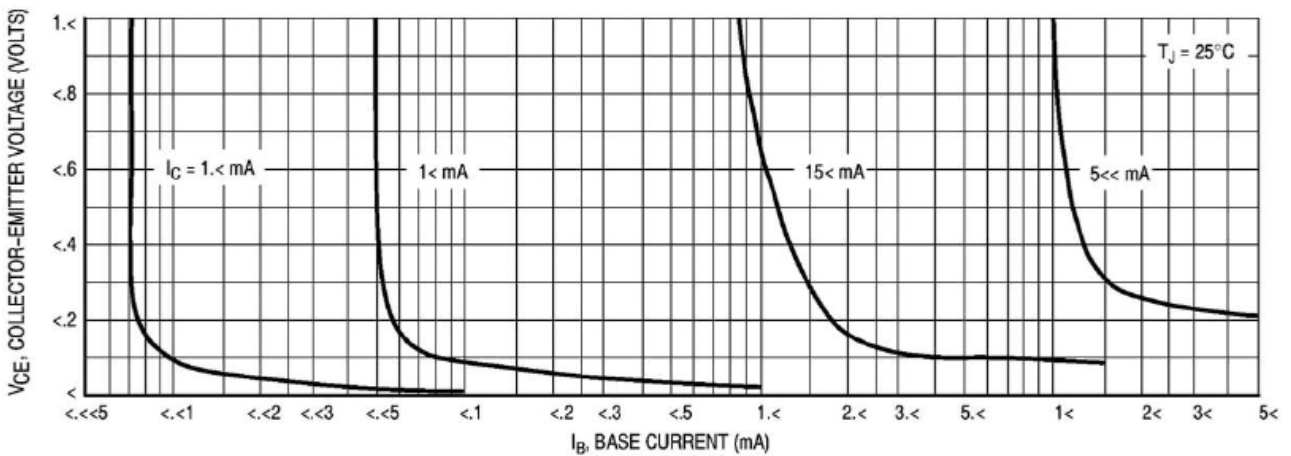




Figure. 5 Turn-on Time

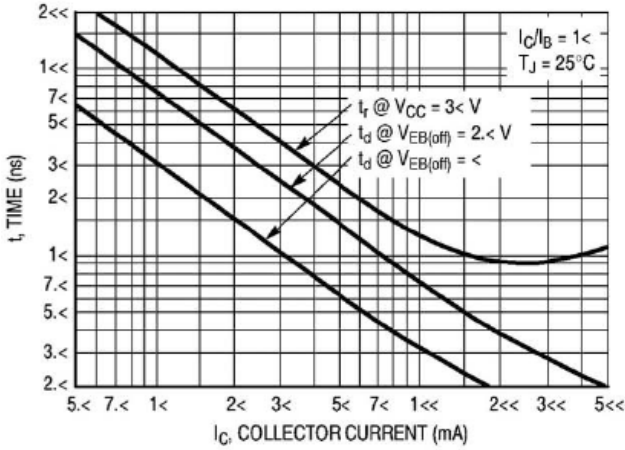


Figure. 6 Turn-off Time

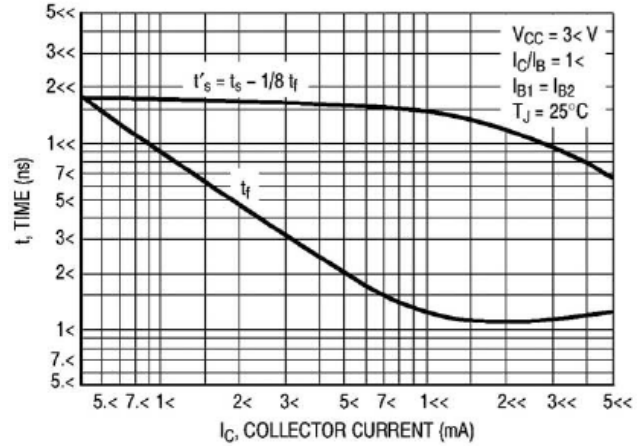


Figure. 7 Frequency Effects

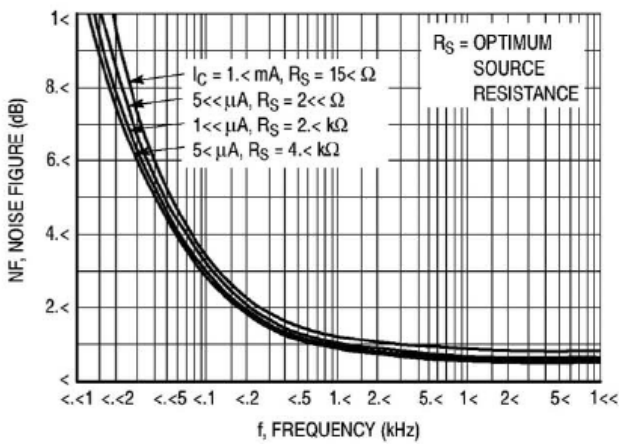


Figure. 8 Source Resistance Effects

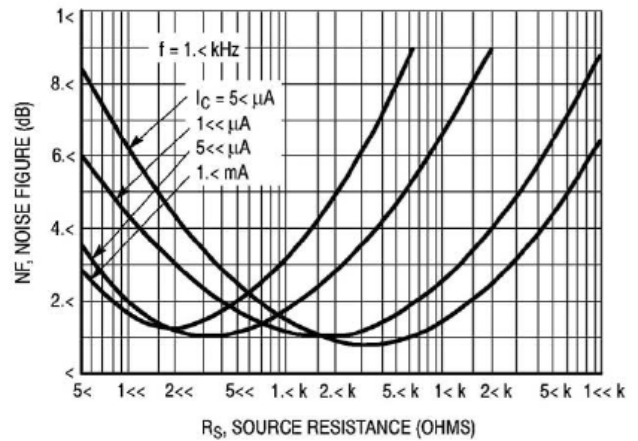


Figure. 9 Capacitances

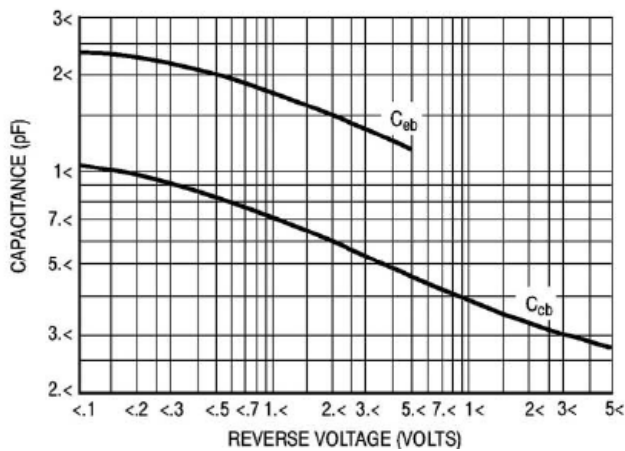


Figure. 10 Current-Gain Bandwidth Product

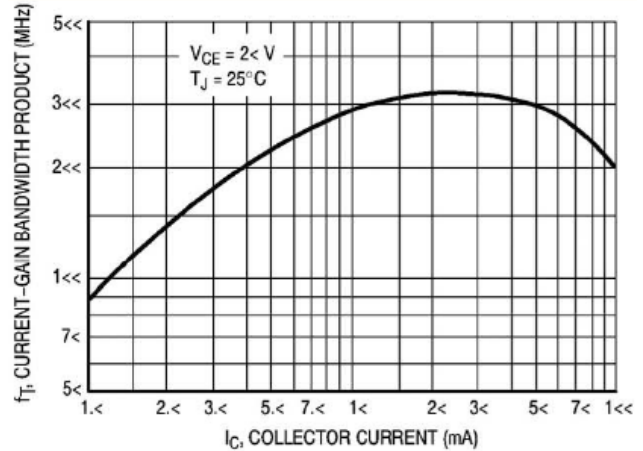
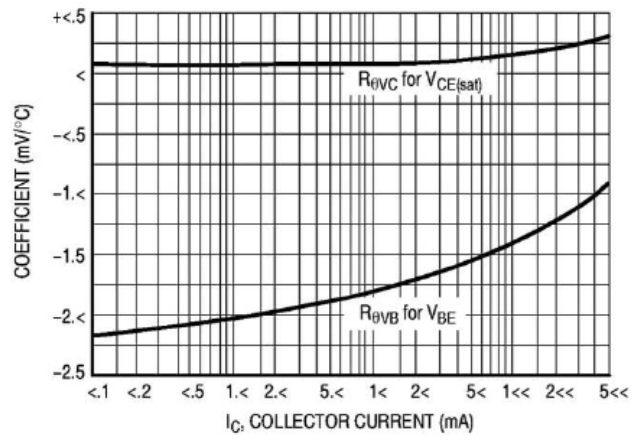
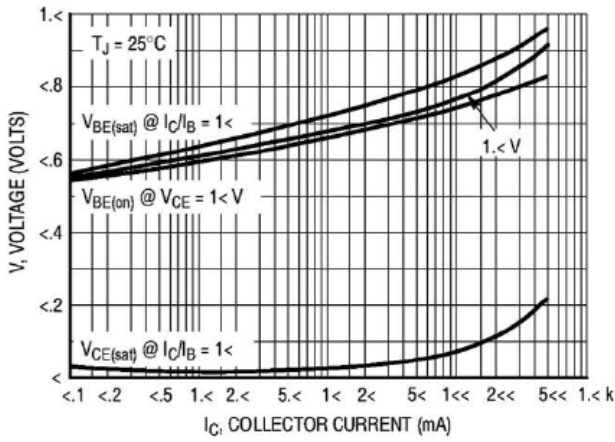


Figure. 11 "On" Voltages

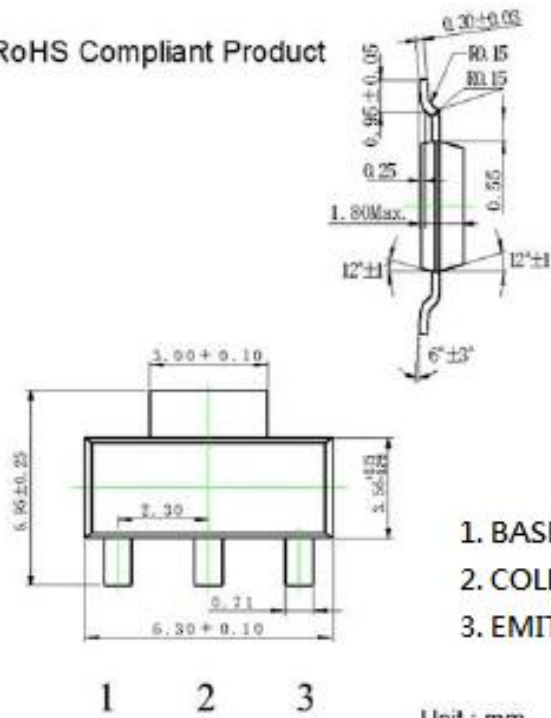
Figure. 12 Temperature Coefficients



## PACKAGE INFORMATION

Dimension in SOT-223 (Unit: mm)

RoHS Compliant Product





## IMPORTANT NOTICE

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